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**CMP METHOD FOR COPPER, TUNGSTEN, TITANIUM, POLYSILICON,
AND OTHER SUBSTRATES USING ORGANOSULFONIC ACIDS AS OXIDIZERS**

ABSTRACT

5 The invention relates to chemical mechanical polishing of substrates using an
abrasive and a fluid composition, wherein certain organosulfonic acid compounds are used as
oxidizers, and particularly relates to a method of polishing substrates comprising copper,
tungsten, titanium, and/or polysilicon using a chemical-mechanical polishing system
comprising organosulfonic acids having an electrochemical oxidation potential greater than
10 0.2V as an oxidizer.